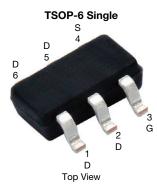
# SQ3481EV

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**Vishay Siliconix** 

# Automotive P-Channel 30 V (D-S) 175 °C MOSFET



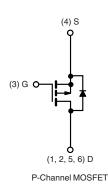
| PRODUCT SUMMARY                            |        |  |  |  |
|--|--------|--|--|--|
| V <sub>DS</sub> (V)                        | - 30   |  |  |  |
| $R_{DS(on)}(\Omega)$ at $V_{GS}$ = - 10 V  | 0.043  |  |  |  |
| $R_{DS(on)}(\Omega)$ at $V_{GS}$ = - 4.5 V | 0.070  |  |  |  |
| I <sub>D</sub> (A)                         | - 7.5  |  |  |  |
| Configuration                              | Single |  |  |  |

### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- AEC-Q101 Qualified<sup>c</sup>
- 100 %  $R_{\rm q}$  and UIS Tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



| ORDERING INFORMATION            |   |
|---------------------------------|---|
| Package                         | TSOP-6  |
| Lead (Pb)-free and halogen-free | SQ3481EV<br>(for detailed order number please see <u>www.vishay.com/doc?79771</u> ) |

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted) |                         |                      |               |    |  |
|--|-------------------------|----------------------|---------------|----|--|
| PARAMETER  | SYMBOL                  | LIMIT                | UNIT          |    |  |
| Drain-Source Voltage   | V <sub>DS</sub>         | - 30                 | V             |    |  |
| Gate-Source Voltage  | Gate-Source Voltage     |                      | ± 20          | V  |  |
| Continuous Drain Current   | T <sub>C</sub> = 25 °C  | I_                   | - 7.5         |    |  |
| Continuous Drain Current   | T <sub>C</sub> = 125 °C | I <sub>D</sub>       | - 4.3         |    |  |
| Continuous Source Current  |                         | I <sub>S</sub>       | - 5.2         | А  |  |
| Pulsed Drain Current <sup>a</sup>  |                         | I <sub>DM</sub>      | - 30          |    |  |
| Single Pulse Avalanche Current   | L = 0.1 mH              | I <sub>AS</sub>      | - 15          |    |  |
| Single Pulse Avalanche Energy  |                         | E <sub>AS</sub>      | 11            | mJ |  |
| Maximum Power Dissipation <sup>a</sup>   | T <sub>C</sub> = 25 °C  | PD                   | 4             | W  |  |
|  | T <sub>C</sub> = 125 °C | ۲D                   | 1.3           | ۷V |  |
| Operating Junction and Storage Temperature Range                                 |                         | TJ, T <sub>stg</sub> | - 55 to + 175 | C° |  |

| THERMAL RESISTANCE RATINGS |                        |                   |       |      |  |
|----------------------------|------------------------|-------------------|-------|------|--|
| PARAMETER                  |                        | SYMBOL            | LIMIT | UNIT |  |
| Junction-to-Ambient        | PCB Mount <sup>b</sup> | R <sub>thJA</sub> | 110   | °C/W |  |
| Junction-to-Foot (Drain)   |                        | R <sub>thJF</sub> | 36    | C/W  |  |

#### Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. When mounted on 1" square PCB (FR-4 material)

c. Parametric verification ongoing

S21-1246-Rev. C, 10-Jan-2022

1

Document Number: 71508

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| PARAMETER                                     | SYMBOL              | TES  | MIN.   | TYP.  | MAX.  | UNIT  |      |  |
|---|---------------------|--|--|-------|-------|-------|------|--|
| Static  | 1                   |  |  |       |       |       |      |  |
| Drain-Source Breakdown Voltage                | V <sub>DS</sub>     | $V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$   |  | - 30  | -     | -     | v    |  |
| Gate-Source Threshold Voltage                 | V <sub>GS(th)</sub> | V <sub>DS</sub> =  | V <sub>GS</sub> , I <sub>D</sub> = - 250 μA                    | - 1.5 | - 2.0 | - 2.5 | v    |  |
| Gate-Source Leakage                           | I <sub>GSS</sub>    | V <sub>DS</sub> =  | $V_{DS} = 0 V, V_{GS} = \pm 20 V$                              |       | -     | ± 100 | nA   |  |
| Zero Gate Voltage Drain Current               |                     | $V_{GS} = 0 V$   | V <sub>DS</sub> = - 30 V                                       | -     | -     | - 1   |      |  |
|   | I <sub>DSS</sub>    | $V_{GS} = 0 V$   | $V_{DS} = -30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$ | -     | -     | - 50  | μA   |  |
|   |                     | $V_{GS} = 0 V$   | $V_{DS}$ = - 30 V, $T_J$ = 175 °C                              | -     | -     | - 150 |      |  |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>  | $V_{GS} = -10 V$   | $V_{DS} \le -5 V$  | - 10  | -     | -     | А    |  |
| Drain-Source On-State Resistance <sup>a</sup> | В                   | $V_{GS} = -10 V$   | I <sub>D</sub> = - 5.3 A                                       | -     | 0.035 | 0.043 | Ω    |  |
| Drain-Source On-State Resistance              | R <sub>DS(on)</sub> | $V_{GS} = -4.5 V$  | I <sub>D</sub> = - 2 A   | -     | 0.055 | 0.070 |      |  |
| Forward Transconductanceb                     | <b>g</b> fs         | V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 5.3 A   |  | -     | 13    | -     | S    |  |
| Dynamic <sup>b</sup>                          |                     |  |  |       |       |       |      |  |
| Input Capacitance                             | C <sub>iss</sub>    |  |  | -     | 695   | 870   | pF   |  |
| Output Capacitance                            | C <sub>oss</sub>    | $V_{GS} = 0 V$   | V <sub>DS</sub> = - 15 V, f = 1 MHz                            | -     | 160   | 200   |      |  |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>    |  |  | -     | 120   | 150   |      |  |
| Total Gate Charge <sup>c</sup>                | Qg                  |  |  | -     | 15.4  | 23.5  |      |  |
| Gate-Source Charge <sup>c</sup>               | Q <sub>gs</sub>     | V <sub>GS</sub> = - 10 V   | $V_{DS} = -15 \text{ V}, \text{ I}_{D} = -5.3 \text{ A}$       | -     | 2.1   |       | nC   |  |
| Gate-Drain Charge <sup>c</sup>                | Q <sub>gd</sub>     |  |  | -     | 3.9   |       |      |  |
| Gate Resistance                               | Rg                  |  | f = 1 MHz  |       | 11.5  | 18.5  | Ω    |  |
| Turn-On Delay Time <sup>c</sup>               | t <sub>d(on)</sub>  |  |  |       | 9     | 14    |      |  |
| Rise Time <sup>c</sup>                        | t <sub>r</sub>      | $V_{DD} = -15 \text{ V}, \text{ R}_{\text{L}} = 15 \Omega$ $\text{I}_{\text{D}} \cong -1 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$ |  | -     | 15    | 23    | - ns |  |
| Turn-Off Delay Time <sup>c</sup>              | t <sub>d(off)</sub> |  |  | -     | 28    | 42    |      |  |
| Fall Time <sup>c</sup>                        | t <sub>f</sub>      |  |  | -     | 12    | 18    |      |  |
|   |                     |  |  |       |       | -     |      |  |
| Pulsed Current <sup>a</sup>                   | I <sub>SM</sub>     |  |  | -     | -     | - 30  | А    |  |
| Forward Voltage                               | V <sub>SD</sub>     | I <sub>F</sub> = ·   | - 1.7 A, V <sub>GS</sub> = 0 V                                 | -     | - 0.8 | - 1.2 | V    |  |

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

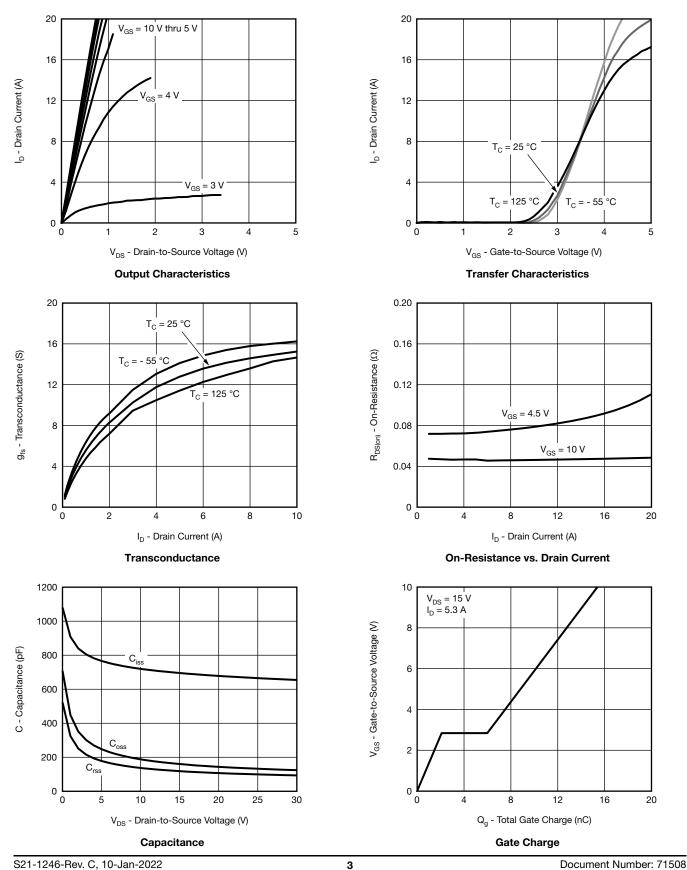
2



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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



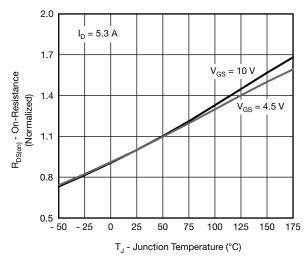
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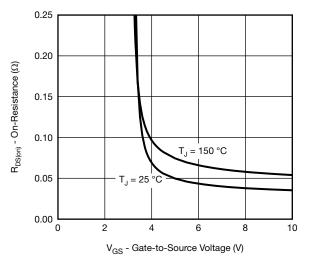


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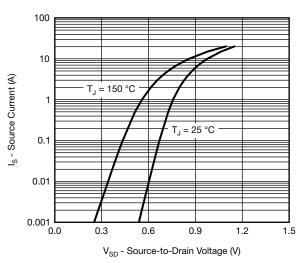
## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



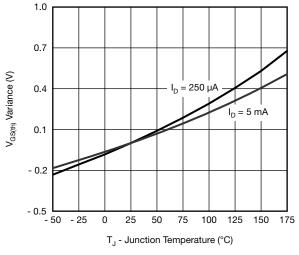




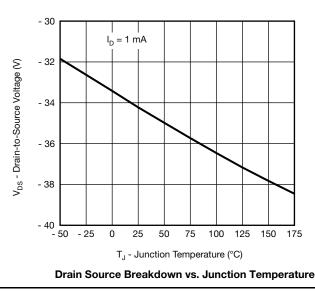
On-Resistance vs. Gate-to-Source Voltage



Source-Drain Diode Forward Voltage







S21-1246-Rev. C, 10-Jan-2022

4

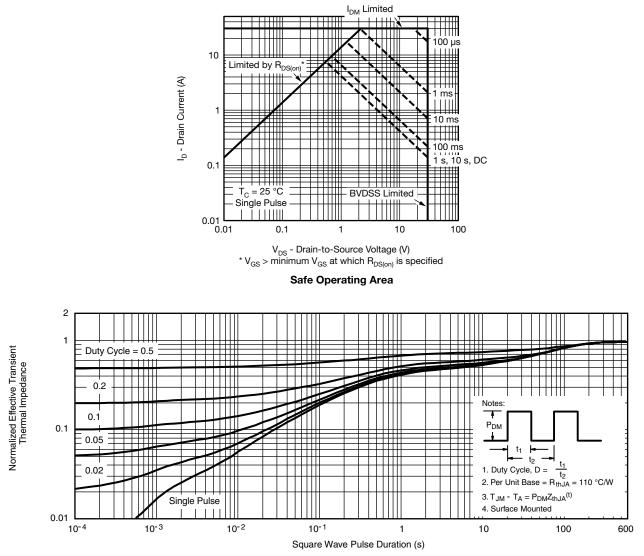
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### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



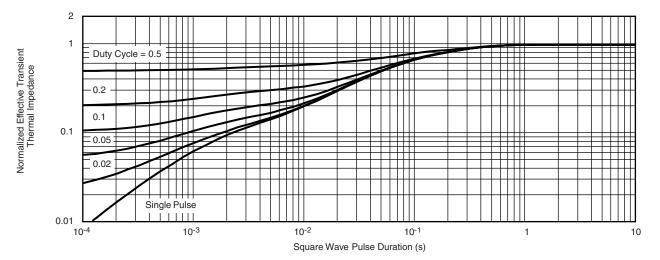
Normalized Thermal Transient Impedance, Junction-to-Ambient



## Vishay Siliconix

Document Number: 71508

### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

The characteristics shown in the two graphs

S21-1246-Rev. C, 10-Jan-2022

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71508.



Package Information

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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



|   | MILLIMETERS |          |      | INCHES |            |       |  |
|---|-------------|----------|------|--------|------------|-------|--|
| Dim   | Min         | Nom      | Max  | Min    | Nom        | Max   |  |
| Α   | 0.91        | -        | 1.10 | 0.036  | -          | 0.043 |  |
| <b>A</b> <sub>1</sub>                       | 0.01        | -        | 0.10 | 0.0004 | -          | 0.004 |  |
| A <sub>2</sub>                              | 0.90        | -        | 1.00 | 0.035  | 0.038      | 0.039 |  |
| b   | 0.30        | 0.32     | 0.45 | 0.012  | 0.013      | 0.018 |  |
| С   | 0.10        | 0.15     | 0.20 | 0.004  | 0.006      | 0.008 |  |
| D   | 2.95        | 3.05     | 3.10 | 0.116  | 0.120      | 0.122 |  |
| Е   | 2.70        | 2.85     | 2.98 | 0.106  | 0.112      | 0.117 |  |
| E <sub>1</sub>                              | 1.55        | 1.65     | 1.70 | 0.061  | 0.065      | 0.067 |  |
| е   |             | 0.95 BSC |      |        | 0.0374 BSC |       |  |
| <b>e</b> <sub>1</sub>                       | 1.80        | 1.90     | 2.00 | 0.071  | 0.075      | 0.079 |  |
| L   | 0.32        | -        | 0.50 | 0.012  | -          | 0.020 |  |
| L <sub>1</sub>                              |             | 0.60 Ref |      |        | 0.024 Ref  |       |  |
| L <sub>2</sub>                              | 0.25 BSC    |          |      |        | 0.010 BSC  |       |  |
| R   | 0.10        | -        | -    | 0.004  | -          | -     |  |
| θ   | 0°          | 4°       | 8°   | 0°     | 4°         | 8°    |  |
| $\theta_1$                                  | 7° Nom      |          |      |        | 7° Nom     |       |  |
| ECN: C-06593-Rev. I, 18-Dec-06<br>DWG: 5540 |             |          |      |        |            |       |  |

## **PAD** Pattern



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# **Recommended Land Pattern For TSOP-5L / TSOP-6L**





TSOP 5L





### Note

• All dimensions are in inches (millimeter)

| ECN: C22-0860-Rev. B, 24-Oct-2022 |  |
|-----------------------------------|--|
| DWG: 3010                         |  |

1



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1